AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A process for fabricating electronic components, in which a support material is provided, which comprises a first and a second surface; a first anodizing operation is carried out along a first direction on the first surface of said support material in order to form at least one first pore that extends, in this support material, along the first direction, further comprising a second anodizing operation carried out along a second direction on the second surface in order to form on the second surface at least one second pore that extends in the support material along said second direction, different from the first direction.

2. (Previously Presented) The process as claimed in claim 1, wherein an insulating material is formed in the first pore.

3. (Previously Presented) The process as claimed in claim 1, wherein an active material is formed in the second pore.

4. (Previously Presented) The process as claimed in claim 3, wherein the active material is chosen from a conductor, a semiconductor, a superconductor, a magnetic material and a carbon structure.

5. (Previously Presented) The process as claimed in claim 3, wherein the active material is deposited in the second pore by electrodeposition.

6. (Previously Presented) The process as claimed in claim 5, wherein the active material is a semiconductor material transparent to light.

7. (Previously Presented) The process as claimed in claim 6, wherein the semiconductor material is an organic material.

8. (Previously Presented) The process as claimed in claim 1, wherein the support material constitutes both a self-supporting structure for a components and electrical contact means.

9. (Previously Presented) The process as claimed in claim 1, wherein a transistor is produced, the source and drain contacts of which are each at one of the ends of the second pore, respectively, and a gate contact is produced by depositing a conducting material on the surface layer.

10. (Previously Presented) The process as claimed in claim 1, wherein the support material is in the form of a portion of a wire extending longitudinally parallel to the second direction.

11. (Previously Presented) The process as claimed in the claim 10, wherein a plurality of pores, including the first pore, are formed, each extending substantially over the thickness of a surface layer of the wire, radically perpendicular to the second direction.

12. (Previously Presented) The process as claimed in claim 11, wherein the surface layer of the wire constitutes a layer of dielectric.

13. (Previously Presented) The process as claimed in claim 1, wherein at least one active element is enveloped in a matrix comprising the support material.

14. (Previously Presented) The process as claimed in claim 13, wherein an electrically conducting material is deposited in at least one of the first and second pores.

15. (Previously Presented) The process as claimed in claim 13, wherein a thermally conducting material is deposited in at least one of the first and second pores.

16. (Previously Presented) The process as claimed in claim 13, wherein an optically conducting material is deposited in at least one of the first and second pores.

17. (Previously Presented) The process as claimed in claim 13, wherein at least one line of a material chosen from an electrically conducting material, a thermally conducting material and an optically conducting material is produced on the surface of the support material, in order to connect the active element to an external element.

18. (Previously Presented) The process as claimed in claim 1, wherein at least three treatment steps take place in a liquid medium, including the first anodizing operation, the second anodizing operation and an electrodeposition step.

19. (Currently Amended) An electronic component obtained by a process in which a support material is provided, which comprises a first and a second surface; a first anodizing operation is carried out along a first direction on the first surface of said support material in order to form at least one first pore that extends, in this support material, along the first direction; a second anodizing operation is carried out along a second direction on the second surface in order to form on the second surface at least one second pore that extends in the support material along said second direction, different from the first direction, the electronic component thereby comprising an element of support material with at least one first pore that extends from the first surface along said first direction and at least one second pore that extends from the second surface along said second direction, different from the first direction.

20. (Previously Presented) The component as claimed in claim 19, wherein the second pore is at least partly filled with an active material.

21. (Previously Presented) The component as claimed in claim 20, wherein the active material is chosen from a conductor, a semiconductor, a superconductor, a magnetic material and a carbon structure.

22. (Previously Presented) The component as claimed in claim 20, wherein the active material is transparent to light.

23. (Previously Presented) The component as claimed in claim 20, wherein the active material is an organic material.

24. (Previously Presented) The component as claimed in claim 20, wherein a first electrical contact is produced between the active material and the support material, on the bottom of the second pore.

25. (Previously Presented) The component as claimed in claim 19, wherein the support material constitutes both a self-supporting structure for the component and electrical contact means.

26. (Previously Presented) The component as claimed in claim 19, wherein the element of support material is in the form of a wire portion that extends longitudinally parallel to the second direction.

27. (Previously Presented) The component as claimed in claim 26, wherein the wire portion includes, at the second pore, a surface layer consisting of an electrically insulating material.

28. (Previously Presented) The component as claimed in claim 27, wherein a second electrical contact, radically external with respect to the surface layer, is produced on this surface layer.

29. (Previously Presented) The component as claimed in claim 19, further including at least one active element connected via the first and second pores to the surface of the support material.

30. (Newly Added) An electronic component obtained by a process in which a support material is provided, which comprises a first and a second surface; a first anodizing operation is carried out along a first direction on the first surface of said support material in order to form at least one first pore that extends, in this support material, along the first direction; a second anodizing operation is carried out along a second direction on the second surface in order to form on the second surface at least one second pore that extends in the support material along said second direction, different from the first direction, the electronic component comprising an element of support material in the form of a wire portion that extends longitudinally parallel to the second direction, with at least one first pore that extends along said first direction, and forming an electrically insulating material and at least one second pore that extends from the second surface along said second direction, different from the first direction, the second pore being at least partly filled with an active material, a first electrical contact being produced between the active material and the support material, on the bottom of the second pore, the wire portion including, at the second pore, a surface layer consisting of said electrically insulating material, a second electrical contact, radially external with respect to the surface layer, being produced on this surface layer.